



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

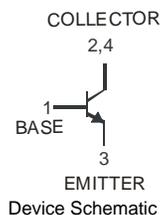
- Complementary PNP Type Available (NK-DSS5540X)
- Ultra Low Collector-Emitter Saturation Voltage
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications

Mechanical Data

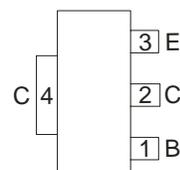
- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Top View



Device Schematic



Pin Out Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	40	V
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	4	A
Repetitive Collector Current (Note 3)	I_{CRM}	5	A
Peak Pulse Collector Current	I_{CM}	10	A
Continuous Base Current	I_B	1	A
Peak Pulse Base Current	I_{BM}	2	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	0.9	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	139	$^\circ\text{C/W}$
Power Dissipation (Note 5) @ $T_A = 25^\circ\text{C}$	P_D	2	W
Thermal Resistance, Junction to Ambient Air (Note 5) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 6)	$V_{(BR)CEO}$	40	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	—	100	nA	$V_{CB} = 30\text{V}, I_E = 0$
		—	—	50	μA	$V_{CB} = 30\text{V}, I_E = 0, T_A = 150^\circ\text{C}$
Collector-Emitter Cut-Off Current	I_{CES}	—	—	100	nA	$V_{CE} = 30\text{V}, V_{BE} = 0\text{V}$
Emitter-Base Cutoff Current	I_{EBO}	—	—	100	nA	$V_{EB} = 5\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 6)						
DC Current Gain	h_{FE}	300	—	—	—	$V_{CE} = 2\text{V}, I_C = 0.5\text{A}$
		300	—	—		$V_{CE} = 2\text{V}, I_C = 1\text{A}$
		250	—	—		$V_{CE} = 2\text{V}, I_C = 2\text{A}$
		100	—	—		$V_{CE} = 2\text{V}, I_C = 5\text{A}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	90	mV	$I_C = 0.5\text{A}, I_B = 5\text{mA}$
		—	—	120		$I_C = 1\text{A}, I_B = 10\text{mA}$
		—	80	150		$I_C = 2\text{A}, I_B = 200\text{mA}$
		—	160	290		$I_C = 4\text{A}, I_B = 200\text{mA}$
		—	185	355		$I_C = 5\text{A}, I_B = 500\text{mA}$
Equivalent On-Resistance	$R_{CE(SAT)}$	—	37	71	m Ω	$I_C = 5\text{A}, I_B = 500\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	1.1	V	$I_C = 4\text{A}, I_B = 200\text{mA}$
		—	—	1.2		$I_C = 5\text{A}, I_B = 500\text{mA}$
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	1.1	V	$V_{CE} = 2\text{V}, I_C = 2\text{A}$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	70	—	—	MHZ	$V_{CE} = 10\text{V}, I_C = 0.1\text{A}, f = 100\text{MHz}$
Collector Capacitance	C_C	—	—	75	pF	$V_{CB} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$
SWITCHING CHARACTERISTICS						
Turn-On Time	t_{on}	—	135	—	ns	$V_{CC} = 10\text{V}, I_C = 2\text{A}, I_{B1} = 40\text{mA}$
Delay Time	t_d	—	60	—	ns	
Rise Time	t_r	—	75	—	ns	
Turn-Off Time	t_{off}	—	670	—	ns	$V_{CC} = 10\text{V}, I_C = 2\text{A}, I_{B1} = I_{B2} = 40\text{mA}$
Storage Time	t_s	—	570	—	ns	
Fall Time	t_f	—	100	—	ns	

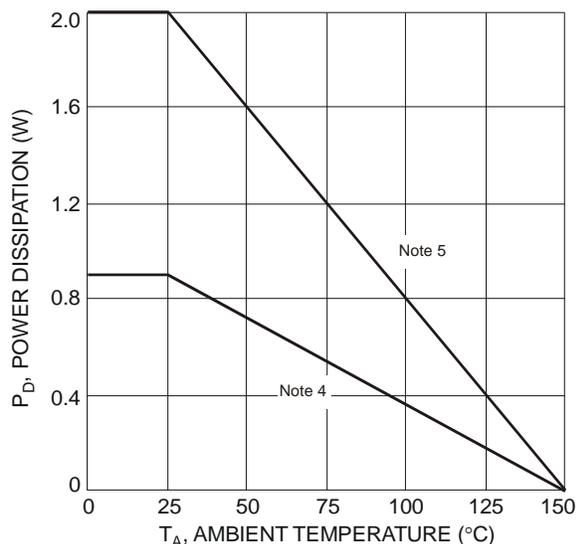
 Notes: 6. Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$.


Fig. 1 Power Dissipation vs. Ambient Temperature

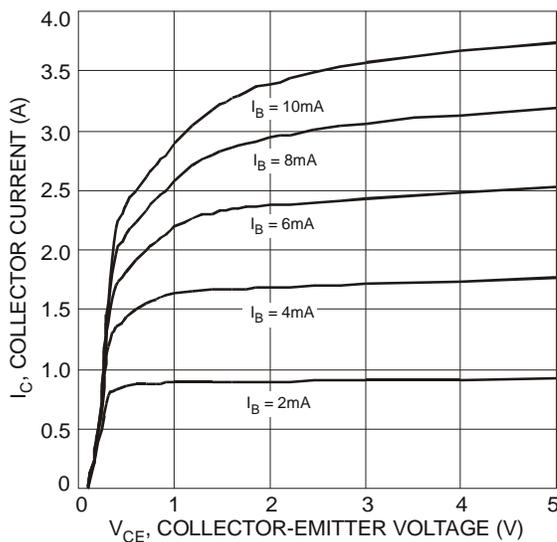


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

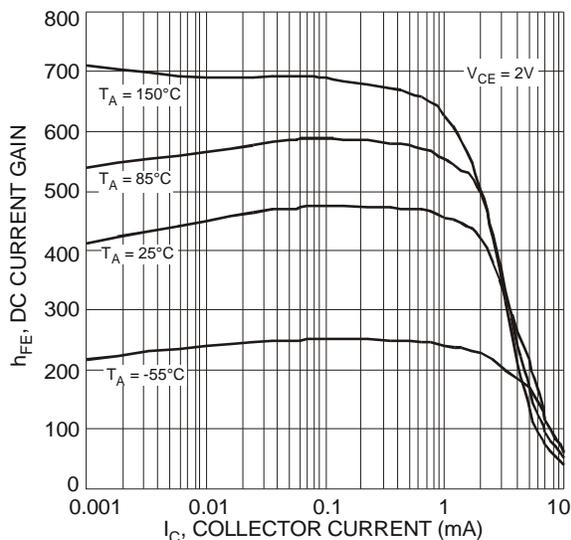


Fig. 3 Typical DC Current Gain vs. Collector Current

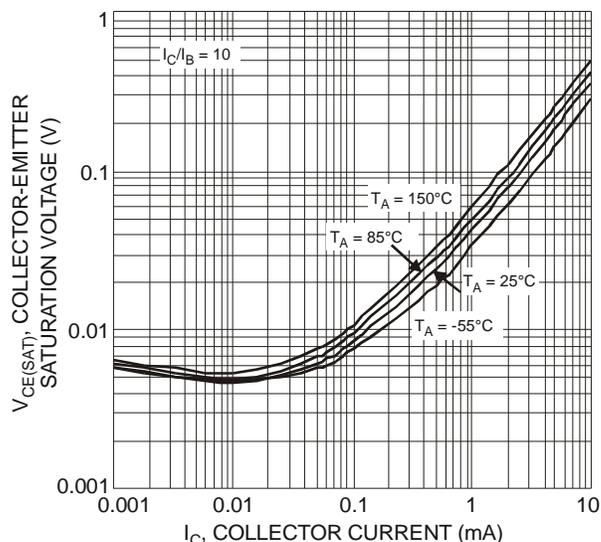


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

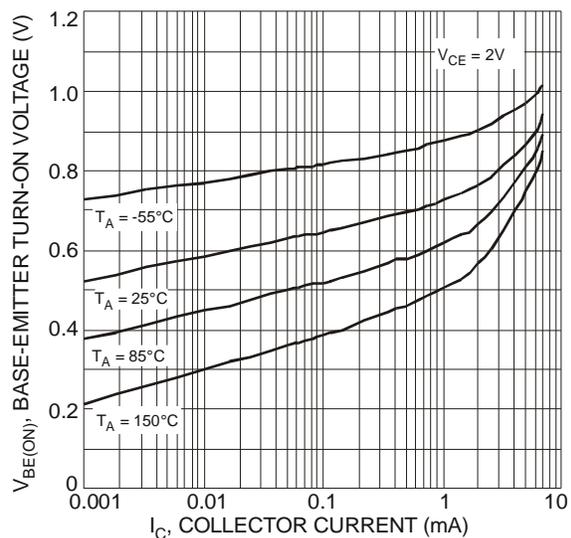


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

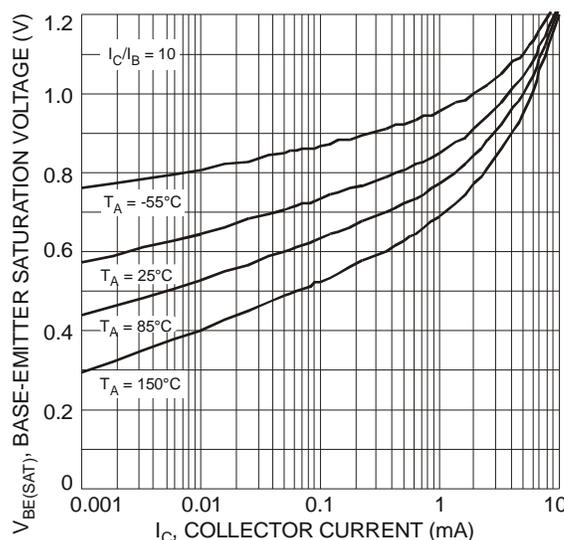


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

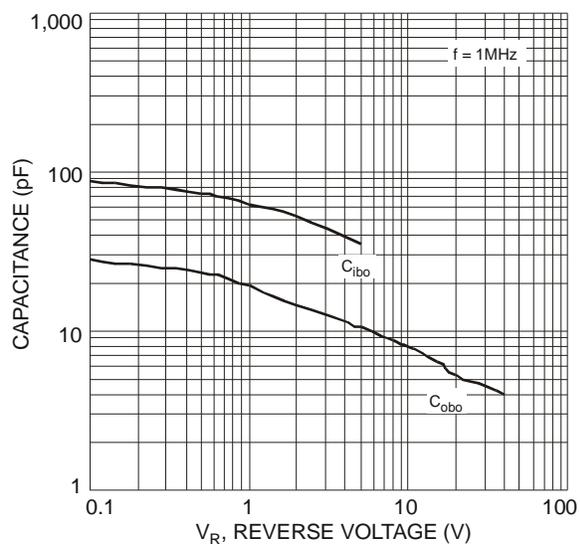


Fig. 7 Typical Capacitance Characteristics

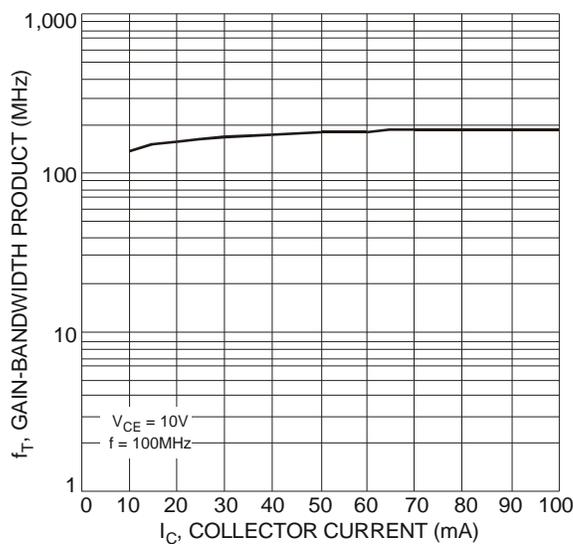
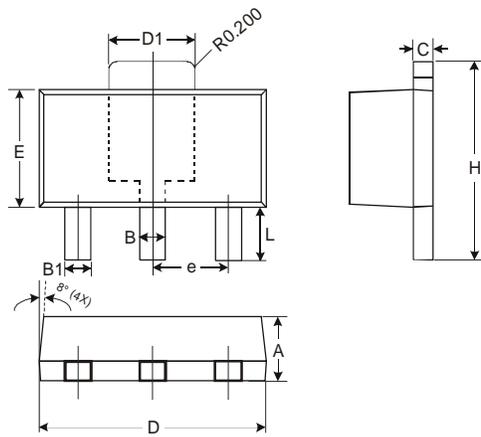


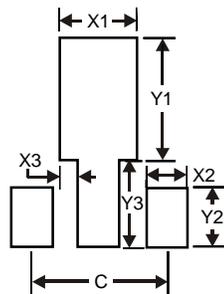
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X1	1.7
X2	0.9
X3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
C	3.0